

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VMB80-28S** is Designed for

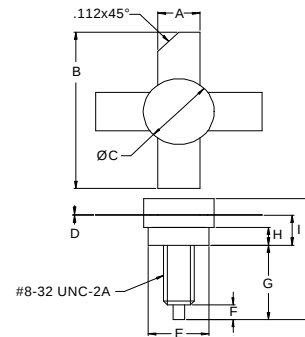
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CBO}	65 V
V_{CEO}	36 V
V_{EBO}	4.0 V
P_{DISS}	103 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.05 $^\circ\text{C/W}$

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10749

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$	36			V
BV_{CES}	$I_C = 20\text{ mA}$	65			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 28\text{ V}$			10	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	5.0		--	---
C_{OB}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			200	pF
P_G η_C	$V_{CC} = 28\text{ V}$ $P_{OUT} = 80\text{ W}$ $f = 88\text{ MHz}$	10	60		dB %